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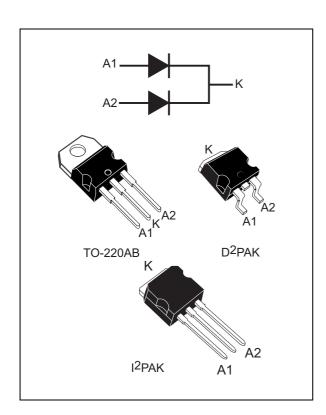




## FERD30M45C

#### Field effect rectifier

Datasheet - production data



#### **Description**

This dual center tap field effect rectifier provides stable leakage current over the full range of reverse voltage and low forward voltage drop.

Packaged in TO-220AB, I<sup>2</sup>PAK or D<sup>2</sup>PAK, this device is intended to be used in solar bypass junction boxes and in switch mode power supplies.

**Table 1. Device summary** 

Symbol	Value
I <sub>F(AV)</sub>	2 x 15 A
V <sub>RRM</sub>	45 V
T <sub>j (max)</sub>	+175 °C (up to 200 °C forward mode only on D²PAK)
V <sub>F</sub> (typ)	0.35 V

#### **Features**

- · Advanced rectifier proprietary process
- · Stable leakage current over reverse voltage
- Reduce leakage current
- Low forward voltage drop
- High frequency operation

Characteristics FERD30M45C

### 1 Characteristics

Table 2. Absolute ratings (limiting values, per diode, at 25 °C, unless otherwise specified)

Symbol	Parameter			Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage			45	V
I <sub>F(RMS)</sub>	Forward rms current			30	Α
Average forward current 8 – 0.5	Average forward current, $\delta = 0.5$	T <sub>c</sub> = 155 °C	Per diode	15	Α
'F(AV)	$I_{F(AV)}$ Average forward current, $\delta = 0.5$	T <sub>c</sub> = 155 °C	Per device	30	
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			250	Α
T <sub>stg</sub>	Storage temperature range			-65 to + 175	°C
$T_j$	Maximum operating junction temperature			175	°C
T <sub>j</sub>	Maximum operating temperature on $D^2PAK$ (DC forward current without reverse bias, $t = 1 \text{ hour}$ ) <sup>(1)</sup>		200	°C	

 $<sup>1. \</sup>quad \tfrac{dPtot}{dTj} < \tfrac{1}{Rth(j-a)} \text{ condition to avoid thermal runaway for a diode on its own heatsink}.$ 

Table 3. Thermal resistance

Symbol	Parameter	Value (max)	Unit	
В	Junction to case	Per diode	1.6	
R <sub>th(j-c)</sub>		Total	1.05	°C/W
R <sub>th(c)</sub>	Coupling		0.5	

When diodes 1 and 2 are used simultaneously:

 $T_j(diode\ 1) = P(diode\ 1) \times R_{th(j-c)}(per\ diode) + P(diode\ 2) \times R_{th}(c)$ 

FERD30M45C **Characteristics** 

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Payaraa laakaga aurrant	T <sub>j</sub> = 25 °C	V V			600	μΑ
I <sub>R</sub> <sup>(1)</sup> Reverse leakage current	T <sub>j</sub> = 125 °C	$V_R = V_{RRM}$		25	50	mA	
	V (2)	T <sub>j</sub> = 125 °C	I <sub>F</sub> = 7.5 A		0.305	0.350	
V <sub>E</sub> <sup>(2)</sup>		T <sub>j</sub> = 125 °C	I <sub>F</sub> = 10 A		0.350	0.395	V
v <sub>F</sub> ( ) Forward voltage drop	Forward voltage drop	T <sub>j</sub> = 25 °C	1 15 1		0.420	0.470	V
		T <sub>i</sub> = 125 °C	I <sub>F</sub> = 15 A		0.420	0.450	

Table 4. Static electrical characteristics (per diode)

- 1. Pulse test:  $t_p = 5$  ms,  $\delta < 2\%$
- 2. Pulse test:  $t_p$  = 380  $\mu$ s,  $\delta$  < 2%

To evaluate the conduction losses use the following equation:

$$P = 0.27 \times I_{F(AV)} + 0.012 I_{F(RMS)}^{2}$$

Figure 1. Average forward power dissipation versus average forward current (per diode)

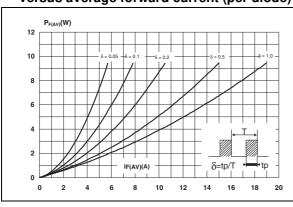


Figure 2. Average forward current versus ambient temperature ( $\delta$  = 0.5, per diode)

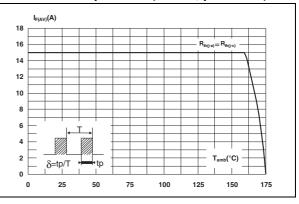
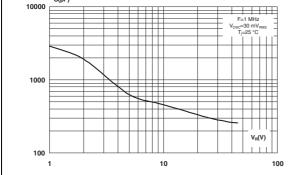
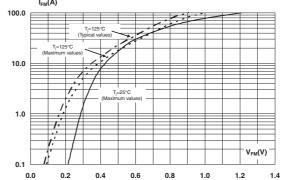


Figure 3. Junction capacitance versus reverse Figure 4. Forward voltage drop versus forward voltage applied (typical values, per diode) current (per diode) I<sub>FM</sub>(A) 10000 100.0

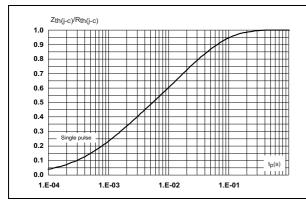


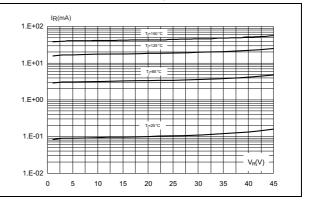


Characteristics FERD30M45C

Figure 5. Relative variation of thermal impedance junction to case versus pulse duration

Figure 6. Reverse leakage current versus reverse voltage applied (typical values, per diode)





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## 2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.8 to 1.0 N·m

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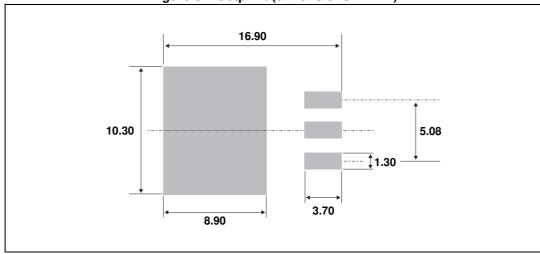
Figure 7. D<sup>2</sup>PAK dimension definitions Е L2 D R \* FLAT ZONE NO LESS THAN 2mm

Package information FERD30M45C

Table 5. D<sup>2</sup>PAK dimension values

	Dimensions					
Ref.	Millin	neters	Inc	hes		
	Min.	Max.	Min.	Max.		
Α	4.40	4.60	0.173	0.181		
A1	2.49	2.69	0.098	0.106		
A2	0.03	0.23	0.001	0.009		
В	0.70	0.93	0.027	0.037		
B2	1.14	1.70	0.045	0.067		
С	0.45	0.60	0.017	0.024		
C2	1.23	1.36	0.048	0.054		
D	8.95	9.35	0.352	0.368		
E	10.00	10.40	0.393	0.409		
G	4.88	5.28	0.192	0.208		
L	15.00	15.85	0.590	0.624		
L2	1.27	1.40	0.050	0.055		
L3	1.40	1.75	0.055	0.069		
М	2.40	3.20	0.094	0.126		
R	0.40	0.40 typ.		6 typ.		
V2	0°	8°	0°	8°		

Figure 8. Footprint (dimensions in mm)



 $\begin{array}{c} & & & \\ & &$ 

Figure 9. TO-220AB dimension definitions

Table 6. TO-220AB dimension values

	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.173	0.181	
С	1.23	1.32	0.048	0.051	
D	2.40	2.72	0.094	0.107	
E	0.49	0.70	0.019	0.027	
F	0.61	0.88	0.024	0.034	
F1	1.14	1.70	0.044	0.066	
F2	1.14	1.70	0.044	0.066	
G	4.95	5.15	0.194	0.202	
G1	2.40	2.70	0.094	0.106	
H2	10	10.40	0.393	0.409	
L2	16.4	typ.	0.645 typ.		
L4	13	14	0.511	0.551	
L5	2.65	2.95	0.104	0.116	
L6	15.25	15.75	0.600	0.620	
L7	6.20	6.60	0.244	0.259	
L9	3.50	3.93	0.137	0.154	
М	2.6 typ.		0.102	typ.	
Diam.	3.75	3.85	0.147	0.151	

Package information FERD30M45C

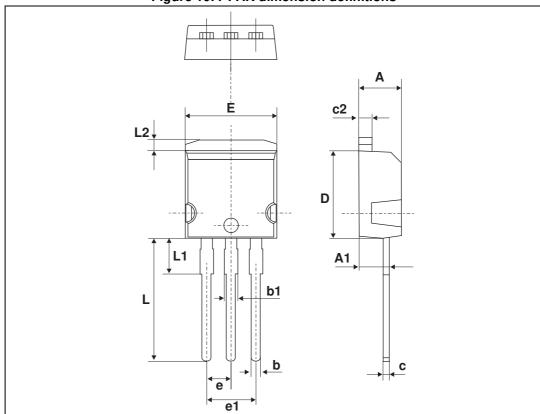


Figure 10. I<sup>2</sup>PAK dimension definitions

Table 7. I<sup>2</sup>PAK dimension values

	Dimensions				
Ref.	Millim	neters	Inches		
	Min.	Max.	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
A1	2.40	2.72	0.094	0.107	
b	0.61	0.88	0.024	0.035	
b1	1.14	1.70	0.044	0.067	
С	0.49	0.70	0.019	0.028	
c2	1.23	1.32	0.048	0.052	
D	8.95	9.35	0.352	0.368	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.195	0.203	
E	10	10.40	0.394	0.409	
L	13	14	0.512	0.551	
L1	3.50	3.93	0.138	0.155	
L2	1.27	1.40	0.050	0.055	

# 3 Ordering information

**Table 8. Ordering information** 

Order code	Marking	Package	Weight	Base qty	Delivery mode
FERD30M45CT	FERD30M45CT	TO-220AB	2.2 g	50	Tube
FERD30M45CG-TR	FERD30M45CG	D <sup>2</sup> PAK	1.5 g	1000	Tape and reel
FERD30M45CR	FERD30M45CR	I <sup>2</sup> PAK	1.4 g	50	Tube

# 4 Revision history

Table 9. Document revision history

Date	Revision	Changes
12-Nov-2012	1	Initial release.
12-Nov-2013	2	Updated title.
11-Jul-2014	3	Added I²PAK package.

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